This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-18 (Canceled)

19. (Amended) A shielded interconnect structure for interconnecting plural devices on a printed circuit board, the shielded interconnect structure comprising: a plurality of signal lines, each signal line comprising:

plural at least one first level conductive traces, trace disposed on an upper surface of the printed circuit board, each first level conductive trace being and adapted for electrical connection to one or more of the plural devices;

plural at least one second level conductive traces, trace disposed on a buried level of the printed circuit board;

plural micro-vias providing electrical connection from selected ones of the first level conductive traces to selected ones of the second level conductive traces;

one or more at least one third level conductive traces, trace disposed on a further buried level of the printed circuit board;

plural buried vias providing electrical connection from the third level conductive traces to certain ones of the second level conductive traces;

a conductive shield comprising;

- a top shield layer disposed on an upper surface of the printed circuit board, a conductive side wall, wall electrically connected to the top shield layer, and
- a bottom shield layer, electrically connected to the conductive side wall,

 wall and buried within the printed circuit board at a level beneath

 the further buried level; and

wherein a trench is formed in the printed circuit board surrounding the first level conductive traces, the second level conductive traces, and the third level conductive traces, the conductive side wall being formed on a wall of the trench a plurality of trenches, each trench having at least a portion which is

parallel to at least one of said signal lines and wherein at least one of said trenches is positioned between adjacent signal lines.

- 20. (Amended) The shielded interconnect structure of claim 19, wherein the top shield layer, the conductive side wall, and the bottom shield layer are formed so that the conductive shield is a unitary Faraday cage surrounding the second level conductive traces and the third level conductive traces plurality of signal lines.
- 21. (Original) The shielded interconnect structure of claim 19, wherein the conductive shield and the first, second, and third level conductive traces are formed substantially of copper.

Claims 22-23 Canceled.

24. (New) The shielded interconnect structure of claim 19 wherein the signal

line comprises at least one micro-via which connects the at least one first level conductive trace to the at least one second level conductive trace.

25. (New) The shielded interconnect structure of claim 19 wherein the signal line comprises at least one micro-via which connects the at least one second level conductive trace to the at least one third level conductive trace.

26. (New) The shielded interconnect structure of claim 19 wherein the conductive side wall of the conductive shield comprises a portion of a wall of at least one of the plurality of trenches.